

# NVTFS4C13N

## MOSFET – Power, Single N-Channel, $\mu$ 8FL 30 V, 9.4 m $\Omega$ , 40 A

### Features

- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- NVTFS4C13NWF – Wettable Flanks Product
- NVT Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

**MAXIMUM RATINGS** ( $T_J = 25^\circ\text{C}$  unless otherwise stated)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	30	V
Gate-to-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 4)	$I_D$	14	A
		10	
Power Dissipation $R_{\theta JA}$ (Note 1, 2, 4)	$P_D$	3.0	W
		1.5	
Continuous Drain Current $R_{\theta JC}$ (Note 1, 3, 4)	$I_D$	40	
		28	A
Power Dissipation $R_{\theta JC}$ (Note 1, 3, 4)	$P_D$	26	W
		13	
Pulsed Drain Current	$I_{DM}$	152	A
Operating Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)	$I_S$	24	A
Single Pulse Drain-to-Source Avalanche Energy ( $T_J = 25^\circ\text{C}$ , $I_L = 14 \text{ A}_{pk}$ , $L = 0.1 \text{ mH}$ )	$E_{AS}$	10	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	$T_L$	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Drain) (Notes 1 and 4)	$R_{\theta JC}$	5.8	
Junction-to-Ambient – Steady State (Notes 1 and 2)	$R_{\theta JA}$	50	$^\circ\text{C/W}$

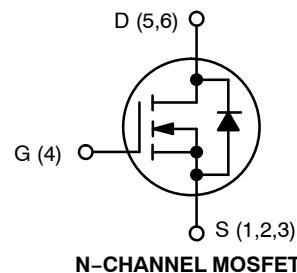
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup> 2 oz. Cu pad.
3. Assumes heat-sink sufficiently large to maintain constant case temperature independent of device power.
4. Continuous DC current rating. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



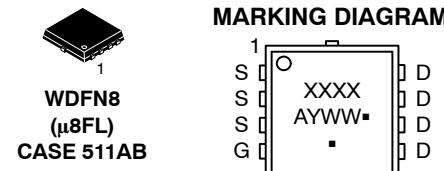
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$V_{(BR)DSS}$	$R_{DS(ON) \text{ MAX}}$	$I_D \text{ MAX}$
30 V	9.4 m $\Omega$ @ 10 V	40 A
	14 m $\Omega$ @ 4.5 V	



N-CHANNEL MOSFET



MARKING DIAGRAM

4C13 = Specific Device Code for NVMTS4C13N  
13WF = Specific Device Code of NVTFS4C13NWF  
A = Assembly Location  
Y = Year  
WW = Work Week  
■ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

# NVTFS4C13N

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>							
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> / T <sub>J</sub>				14.9		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 24 V	T <sub>J</sub> = 25°C		1.0		μA
			T <sub>J</sub> = 125°C		10		
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V				±100	nA
<b>ON CHARACTERISTICS (Note 5)</b>							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA		1.3		2.1	V
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>				4.8		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A		7.5	9.4	mΩ
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 12 A		11.2	14	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 1.5 V, I <sub>D</sub> = 15 A			40		S
Gate Resistance	R <sub>G</sub>	T <sub>A</sub> = 25°C			1.0		Ω
<b>CHARGES AND CAPACITANCES</b>							
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 15 V			770		pF
Output Capacitance	C <sub>OSS</sub>				443		
Reverse Transfer Capacitance	C <sub>rss</sub>				127		
Capacitance Ratio	C <sub>rss</sub> /C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 15 V, f = 1 MHz			0.165		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 15 V; I <sub>D</sub> = 30 A			7.8		nC
Threshold Gate Charge	Q <sub>G(TH)</sub>				1.4		
Gate-to-Source Charge	Q <sub>GS</sub>				2.9		
Gate-to-Drain Charge	Q <sub>GD</sub>				3.7		
Gate Plateau Voltage	V <sub>GP</sub>				3.6		V
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 15 V; I <sub>D</sub> = 30 A			15.2		nC
<b>SWITCHING CHARACTERISTICS (Note 6)</b>							
Turn-On Delay Time	t <sub>d(ON)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A, R <sub>G</sub> = 3.0 Ω			9		ns
Rise Time	t <sub>r</sub>				35		
Turn-Off Delay Time	t <sub>d(OFF)</sub>				13		
Fall Time	t <sub>f</sub>				5		
Turn-On Delay Time	t <sub>d(ON)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A, R <sub>G</sub> = 3.0 Ω			6.0		ns
Rise Time	t <sub>r</sub>				26		
Turn-Off Delay Time	t <sub>d(OFF)</sub>				16		
Fall Time	t <sub>f</sub>				3.0		
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>							
Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 30 A	T <sub>J</sub> = 25°C		0.82	1.1	V
			T <sub>J</sub> = 125°C		0.69		
Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = 0 V, dI <sub>S</sub> /dt = 100 A/μs, I <sub>S</sub> = 30 A			23.4		ns
Charge Time	t <sub>a</sub>				12.1		
Discharge Time	t <sub>b</sub>				11.3		
Reverse Recovery Charge	Q <sub>RR</sub>				9.7		nC

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

6. Switching characteristics are independent of operating junction temperatures.

## TYPICAL CHARACTERISTICS

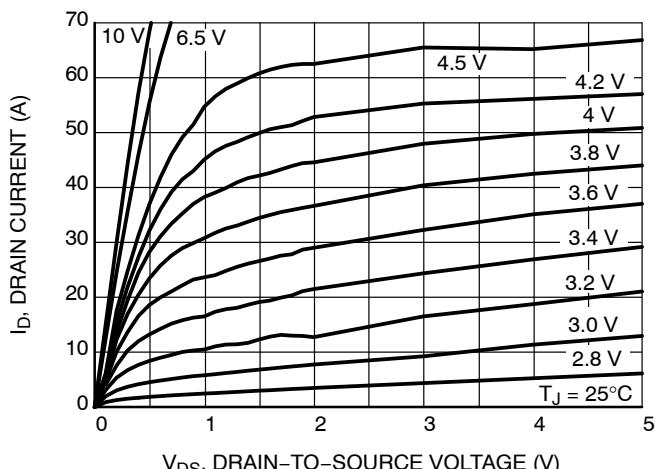


Figure 1. On-Region Characteristics

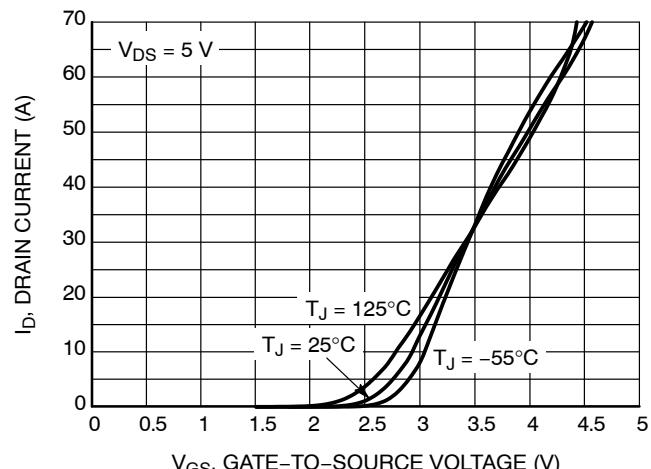


Figure 2. Transfer Characteristics

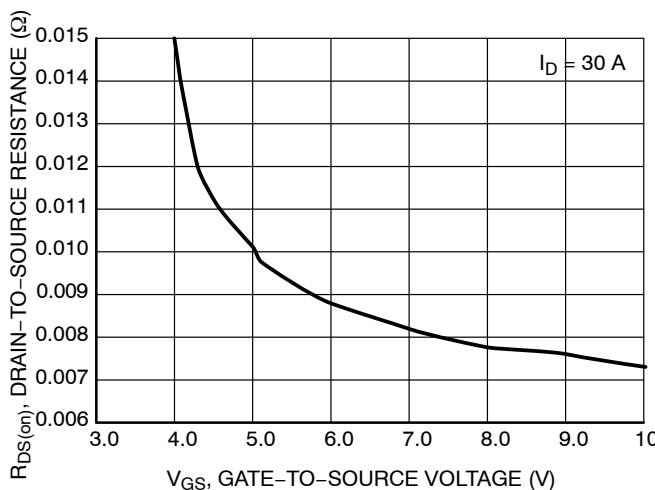


Figure 3. On-Resistance vs.  $V_{GS}$

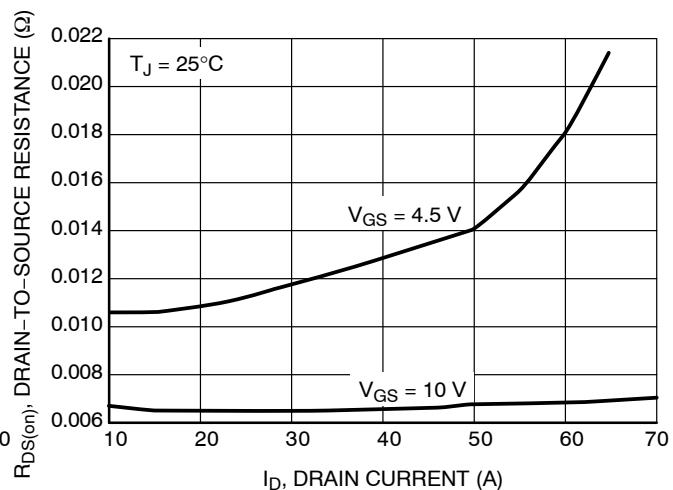


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

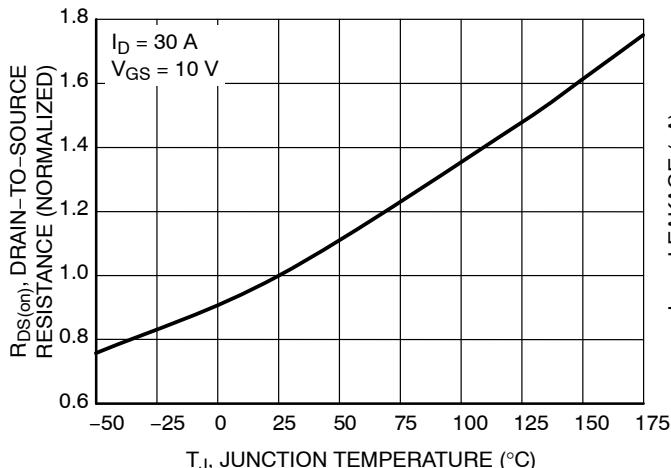


Figure 5. On-Resistance Variation with Temperature

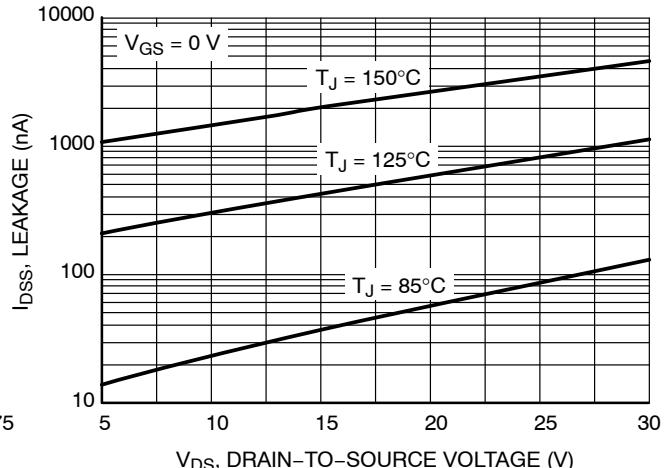


Figure 6. Drain-to-Source Leakage Current vs. Voltage

## TYPICAL CHARACTERISTICS

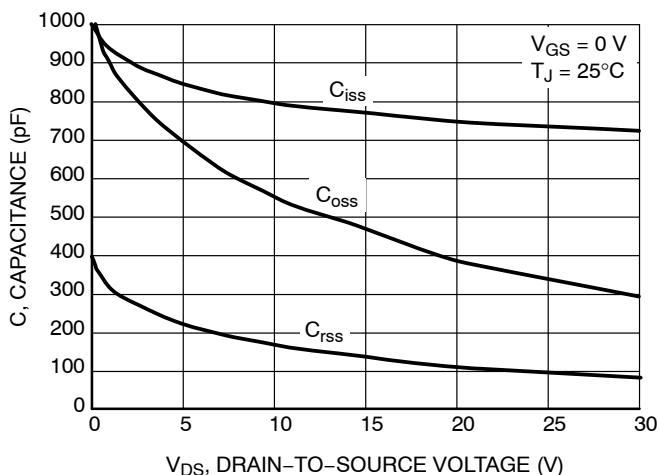


Figure 7. Capacitance Variation

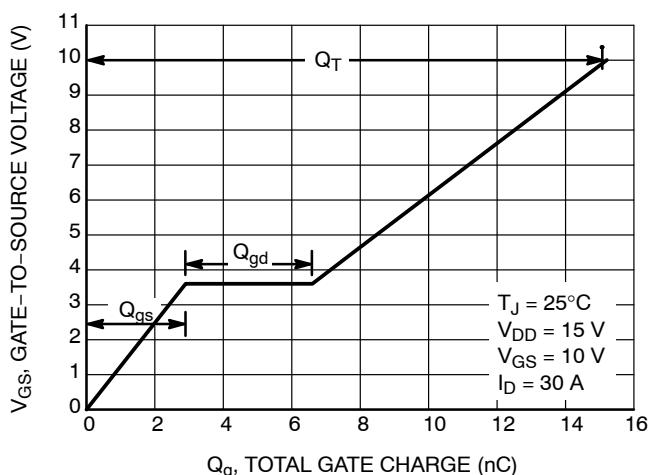


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

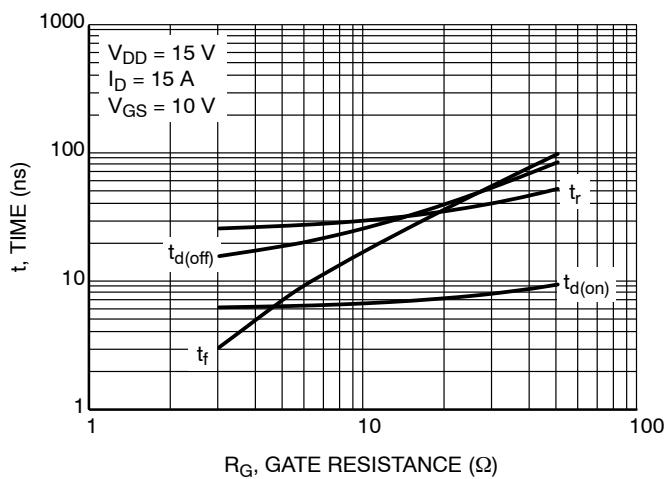


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

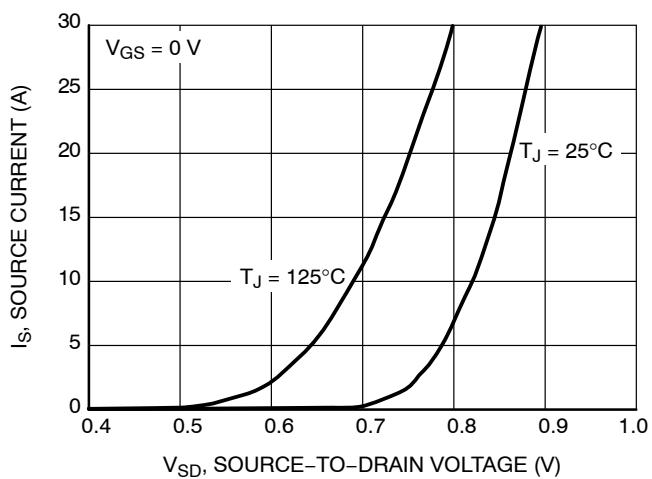


Figure 10. Diode Forward Voltage vs. Current

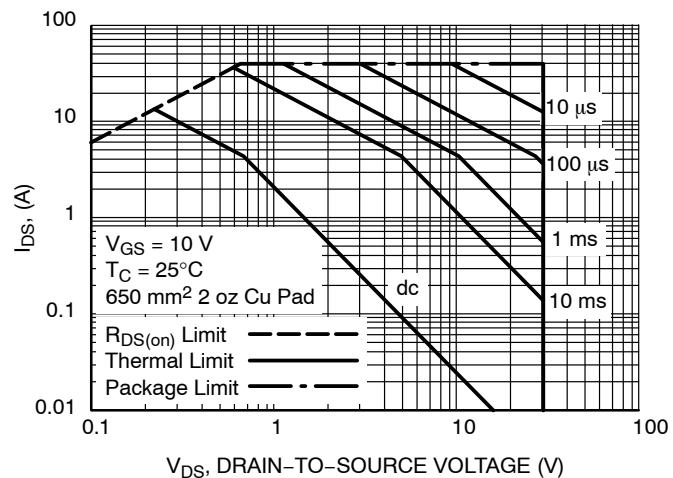


Figure 11. Maximum Rated Forward Biased Safe Operating Area

# NVTFS4C13N

## TYPICAL CHARACTERISTICS

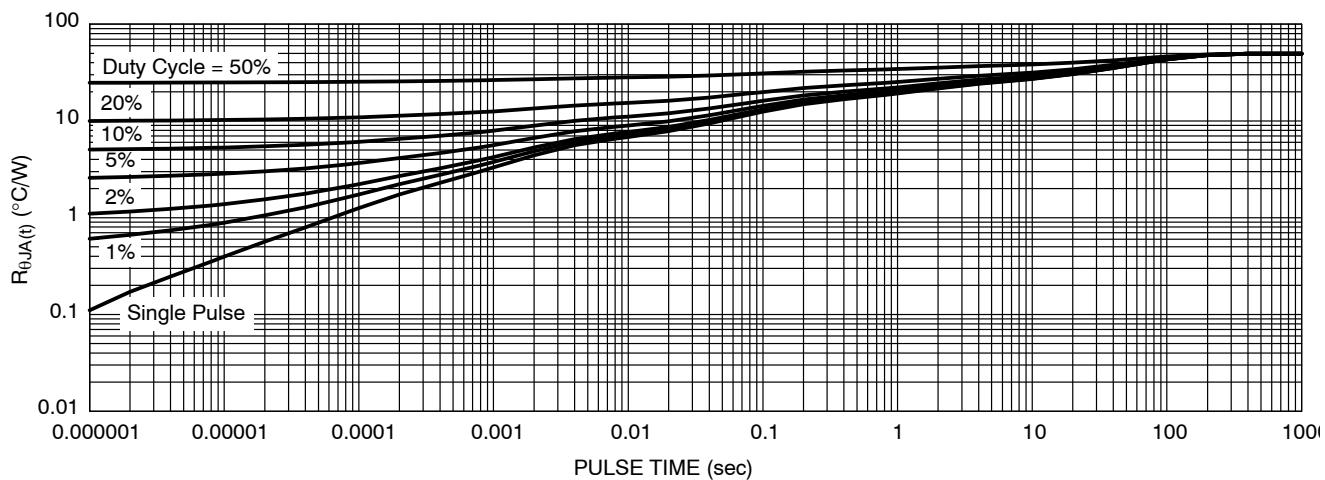


Figure 12. Thermal Response

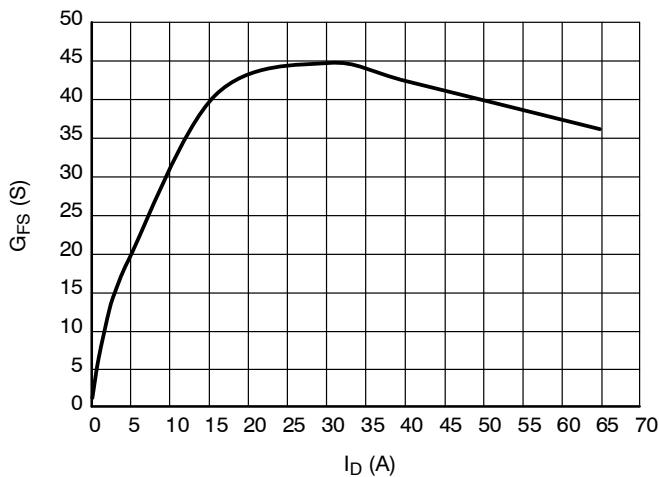


Figure 13.  $G_{FS}$  vs.  $I_D$

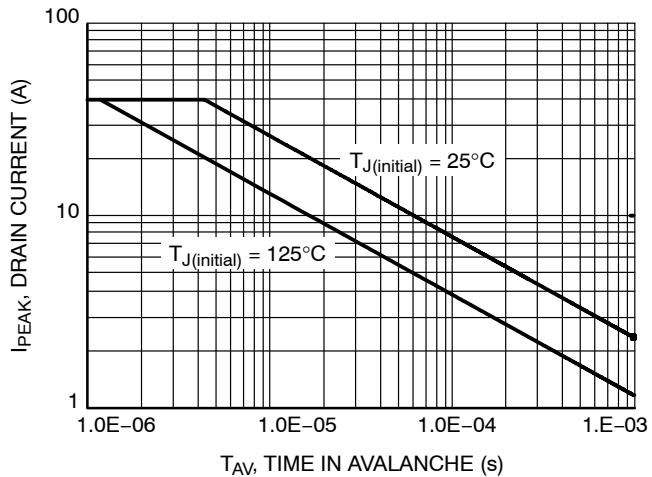


Figure 14. Avalanche Characteristics

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NVTFS4C13NTAG	WDFN8 (Pb-Free)	1500 / Tape & Reel
NVTFS4C13NWFTAG	WDFN8 (Pb-Free)	1500 / Tape & Reel
NVTFS4C13NTWG	WDFN8 (Pb-Free)	5000 / Tape & Reel
NVTFS4C13NWFTWG	WDFN8 (Pb-Free)	5000 / Tape & Reel

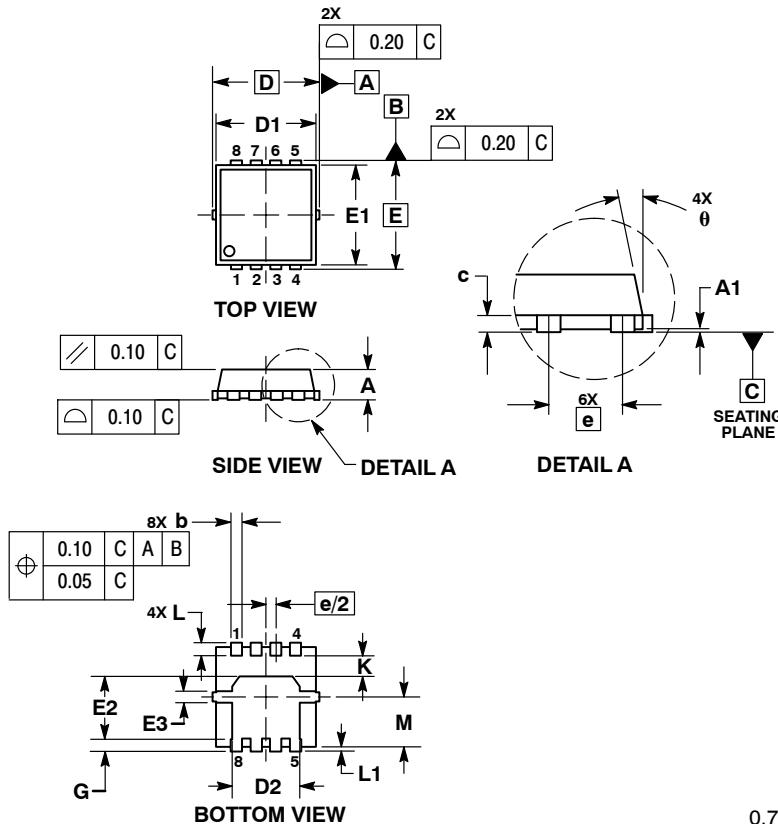
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## PACKAGE DIMENSIONS

## WDFN8 3.3x3.3, 0.65P

CASE 511AB

ISSUE D

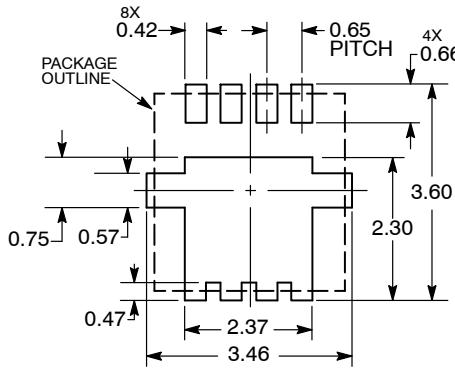


## NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
<b>A</b>	0.70	0.75	0.80	0.028	0.030	0.031
<b>A1</b>	0.00	---	0.05	0.000	---	0.002
<b>b</b>	0.23	0.30	0.40	0.009	0.012	0.016
<b>c</b>	0.15	0.20	0.25	0.006	0.008	0.010
<b>D</b>	3.30 BSC			0.130 BSC		
<b>D1</b>	2.95	3.05	3.15	0.116	0.120	0.124
<b>D2</b>	1.98	2.11	2.24	0.078	0.083	0.088
<b>E</b>	3.30 BSC			0.130 BSC		
<b>E1</b>	2.95	3.05	3.15	0.116	0.120	0.124
<b>E2</b>	1.47	1.60	1.73	0.058	0.063	0.068
<b>E3</b>	0.23	0.30	0.40	0.009	0.012	0.016
<b>e</b>	0.65 BSC			0.026 BSC		
<b>G</b>	0.30	0.41	0.51	0.012	0.016	0.020
<b>K</b>	0.65	0.80	0.95	0.026	0.032	0.037
<b>L</b>	0.30	0.43	0.56	0.012	0.017	0.022
<b>L1</b>	0.06	0.13	0.20	0.002	0.005	0.008
<b>M</b>	1.40	1.50	1.60	0.055	0.059	0.063
<b>θ</b>	0 °	---	12 °	0 °	---	12 °

## SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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